



(19)

(11) Publication number: 07029823 A

Generated Document.

PATENT ABSTRACTS OF JAPAN

(21) Application number: 05154049

(51) Intl. Cl.: H01L 21/203 H01L 21/331 H01L 29/73

(22) Application date: 25.06.93

<p>(30) Priority:</p> <p>(43) Date of application publication: 31.01.95</p> <p>(84) Designated contracting states:</p>	<p>(71) Applicant: NEC CORP</p> <p>(72) Inventor: TAKANO HIROSHI</p> <p>(74) Representative:</p>
--	--

(54) FABRICATION OF
SEMICONDUCTOR
DEVICE

(57) Abstract:

PURPOSE: To shorten the fabrication process of semiconductor device, when epitaxial growth of silicon is conducted selectively by irradiating a silicon substrate with a molecular beam of silicon using a solid source, by simultaneously irradiating the silicon substrate with a molecular beam of solid halide compound.

CONSTITUTION: Silicon oxide 12 is deposited on an n+ type silicon substrate 11 and then an opening 13 is made therein. The silicon substrate 11 is then set on a rotary substrate heating table 2 in a growth chamber 1. Subsequently, the silicon substrate 11 is irradiated simultaneously with molecular beams of silicon, P type impurities and a solid halide compound, i.e., XeF₂ (or XeF₄) by means of an E gun 3 for Si, a K cell 4 and a K cell 5 for solid halide compound. Consequently, silicon is grown selectively and an epitaxial film 14 is formed at the opening 13.

COPYRIGHT: (C)1995,JPO

